

1. PRODUCT Schottky Barrier Diode (Silicon Epitaxial Planar)
2. TYPE **RBQ10BM45A**
3. APPLICATION General rectification
4. FEATURE
 - Power mold type (TO-252)
 - Cathode Common Dual Type
 - High reliability
 - Low IR

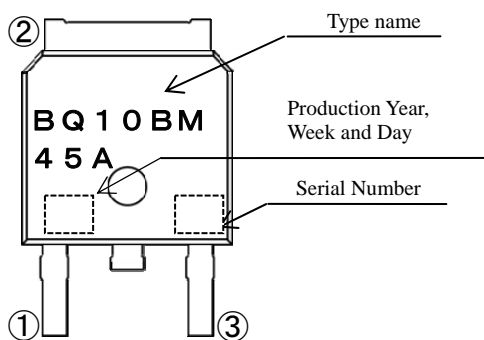
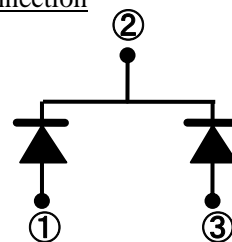
5. ABSOLUTE MAXIMUM RATING (at Tc=25°C unless otherwise specified)

Item	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRM	Duty ≤ 0.5	45	V
Reverse Voltage	VR	Direct reverse voltage	45	V
Average Current	Io	60Hz half sin wave resistive load , 1/2 Io per diode	10	A
Non-repetitive Forward Surge Current	IFSM	60Hz half sin wave, one cycle, non-repetitive at Tj=25°C, per diode	50	A
Operating Junction temperature	Tj	—	150	°C
Storage temperature	Tstg	—	-40 ~ 150	°C

6. ELECTRICAL CHARACTERISTICS (Per diode at Tj=25°C unless otherwise specified)

Characteristic	Symbol	Test Condition	Specification			Unit
			Min.	Typ.	Max.	
Forward Voltage	VF	IF=5A	—	—	0.65	V
Reverse Current	IR	VR=45V	—	—	0.15	mA

*Please pay attention to static electricity when handling.

7. MARKING AND CONNECTION
Marking

Connection


- ① Anode
- ② Cathode
- ③ Anode

Attention in use
 Compared with PN junction diodes, Schottky Barrier Diode generally have higher IR (Reverse leakage current). So that the reverse loss of the diode will increase as temperature increase causing heat up and resulting further increase of IR. This phenomenon will be cause of overheat destruction of the diode. Therefore please give consideration to the reverse loss and around temperature.

DESIGN 	CHECK 	APPROVAL 	DATE: 1.AUG.2013	SPECIFICATION No. : RBQ10BM45A-E
			REV. : A	ROHM Co., Ltd.